

V_{DSS}	20V
$R_{DS(on)}$ (Max.)	180mΩ
I_D	1.5A
P_D	2.0W

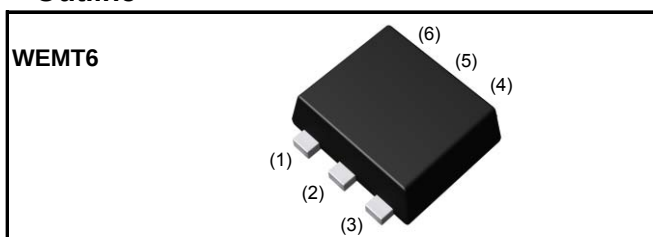
●Features

- 1) Low on - resistance.
- 2) 1.5V Drive.
- 3) Built-in G-S Protection Diode.
- 4) Small Surface Mount Package (WEMT6).
- 5) Pb-free lead plating ; RoHS compliant

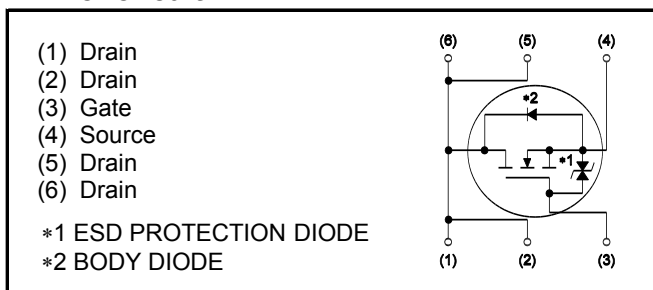
●Application

DC/DC converters

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	8,000
	Taping code	T2R
	Marking	PS

●Absolute maximum ratings($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	20	V
Continuous drain current	I_D^{*1}	± 1.5	A
Pulsed drain current	$I_{D,pulse}^{*2}$	± 3.0	A
Gate - Source voltage	V_{GSS}	± 10	V
Power dissipation	P_D^{*3}	0.7	W
	P_D^{*4}	0.4	W
Junction temperature	T_j	150	$^\circ\text{C}$
Range of storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	179	°C/W
	R_{thJA}^{*4}	-	-	313	°C/W

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	20	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	20	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	0.3	-	1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	-1.9	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 4.5V, I_D = 1.5A$	-	130	180	mΩ
		$V_{GS} = 2.5V, I_D = 1.5A$	-	170	240	
		$V_{GS} = 1.8V, I_D = 0.8A$	-	220	310	
		$V_{GS} = 1.5V, I_D = 0.3A$	-	300	600	
		$V_{GS} = 4.5V, I_D = 1.5A, T_j = 125^\circ\text{C}$	-	200	280	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	25	-	Ω
Transconductance	g_{fs}^{*5}	$V_{DS} = 10V, I_D = 9A$	1.6	3.2	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (15×20×0.8mm)

*5 Pulsed

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	110	-	pF
Output capacitance	C_{oss}	$V_{DS} = 10V$	-	18	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	15	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 15V, V_{GS} = 10V$	-	5	-	ns
Rise time	t_r^{*5}	$I_D = 1A$	-	5	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 10\Omega$	-	20	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	3	-	

●Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 10V, I_D = 91.5A$ $V_{GS} = 4.5V$	-	1.8	-	nC
Gate - Source charge	Q_{gs}^{*5}		-	0.3	-	
Gate - Drain charge	Q_{gd}^{*5}		-	0.3	-	

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_a = 25^\circ\text{C}$	-	-	0.5	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0V, I_S = 1.5A$	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

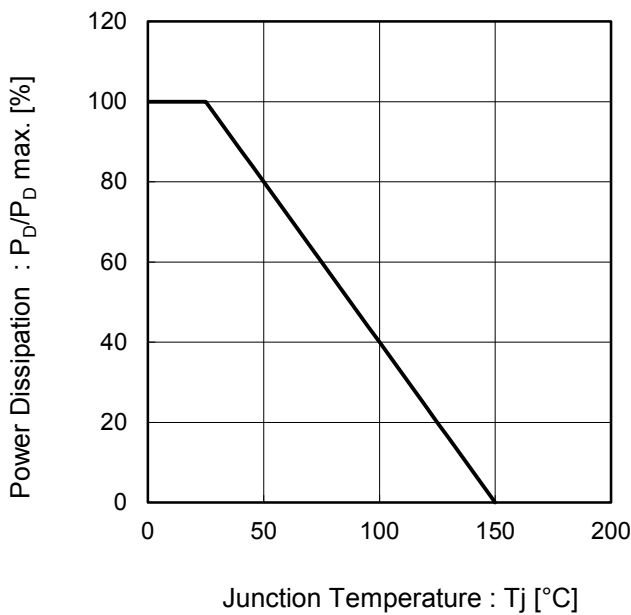


Fig.2 Maximum Safe Operating Area

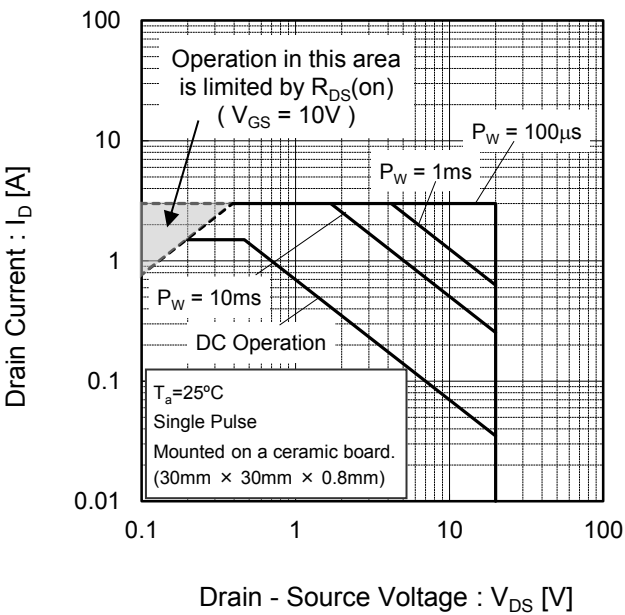


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

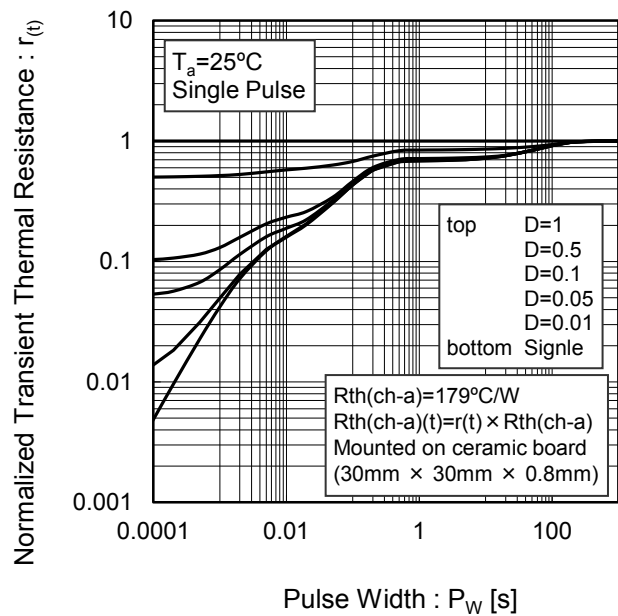
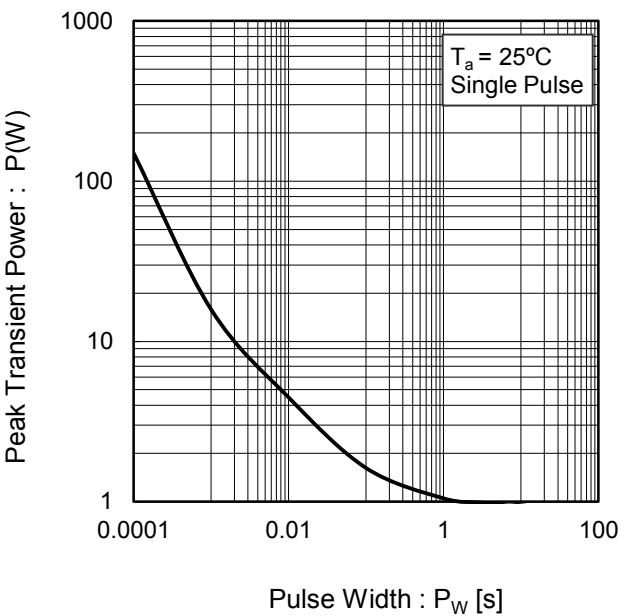


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

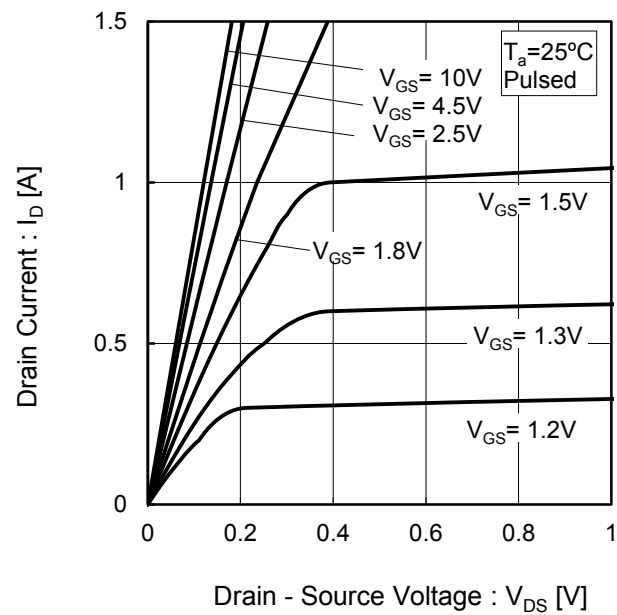


Fig.6 Typical Output Characteristics(II)

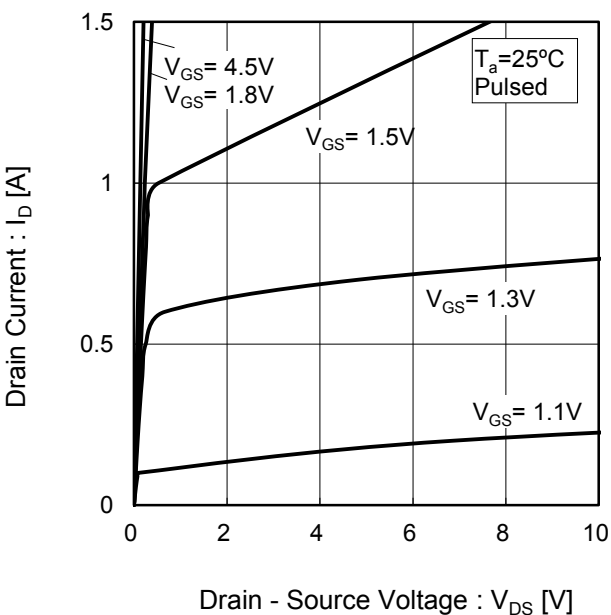


Fig.7 Breakdown Voltage vs. Junction Temperature

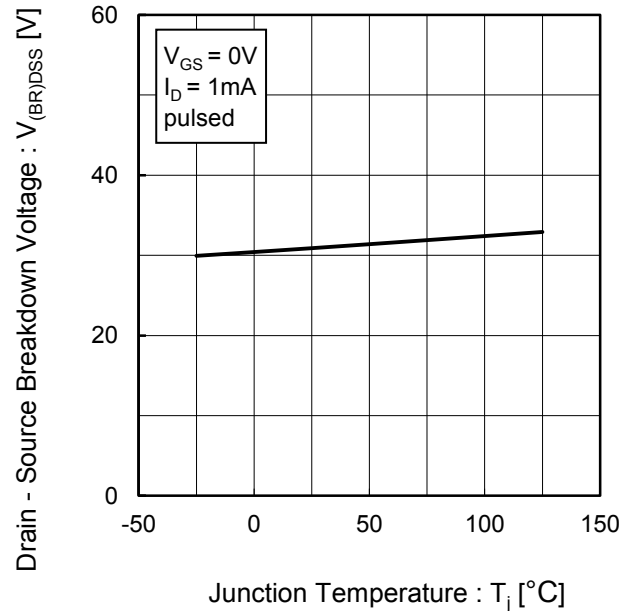
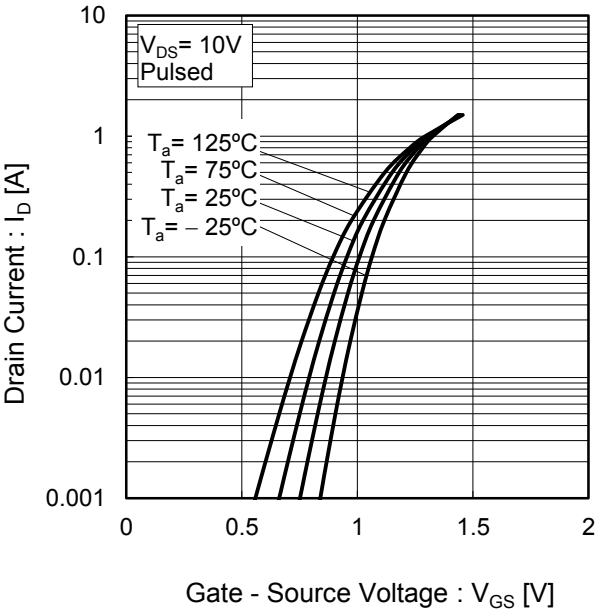


Fig.8 Typical Transfer Characteristics



●Electrical characteristic curves

Fig.9 Gate Threshold Voltage
vs. Junction Temperature

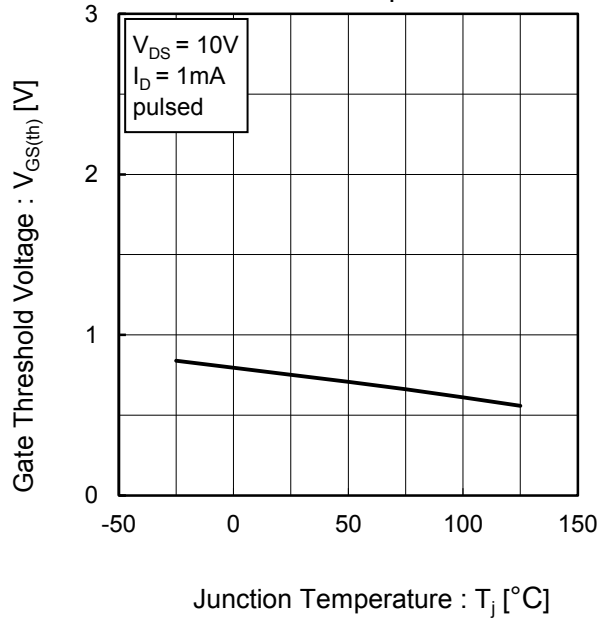


Fig.10 Transconductance vs. Drain Current

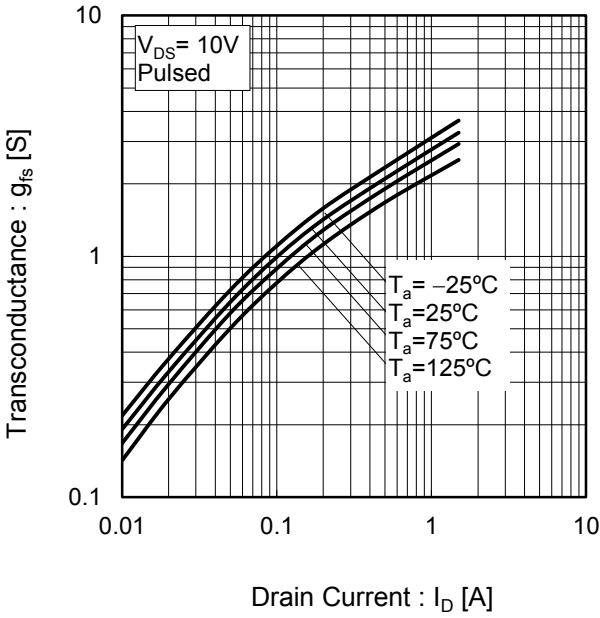


Fig.11 Drain CurrentDerating Curve

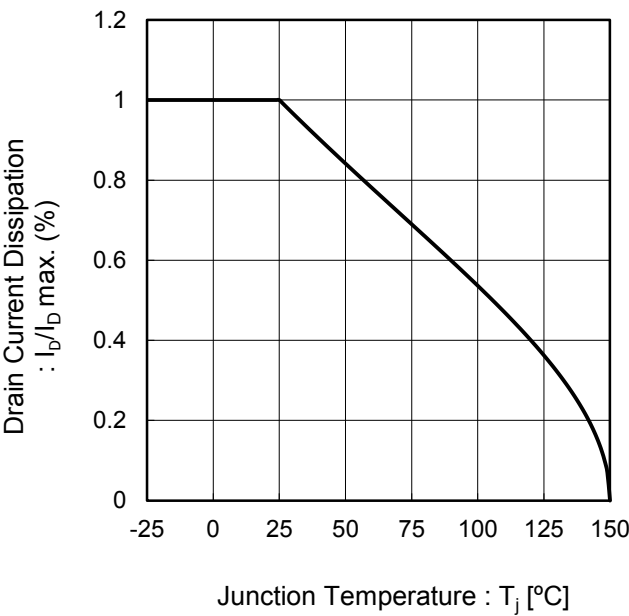
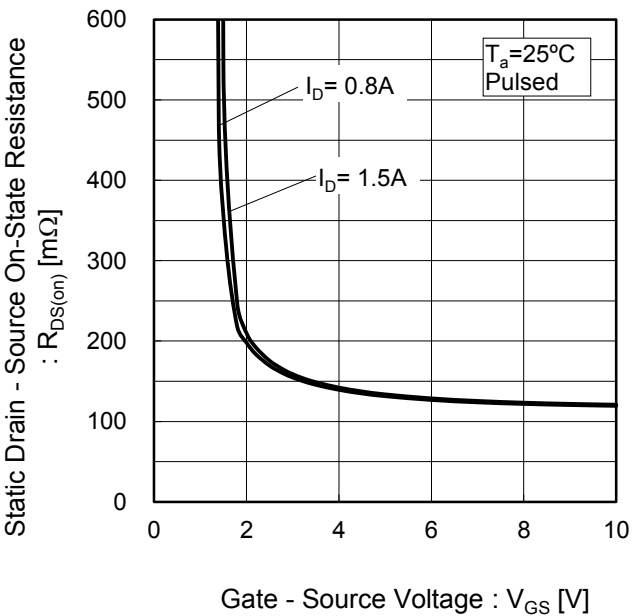


Fig.12 Static Drain - Source On - State
Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

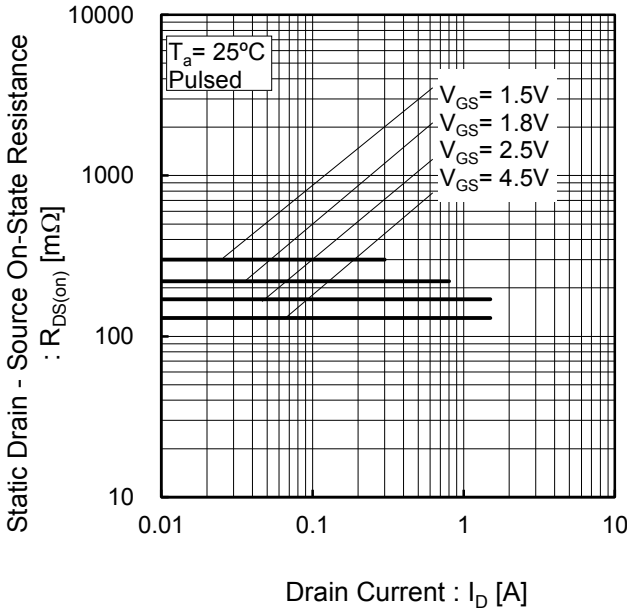
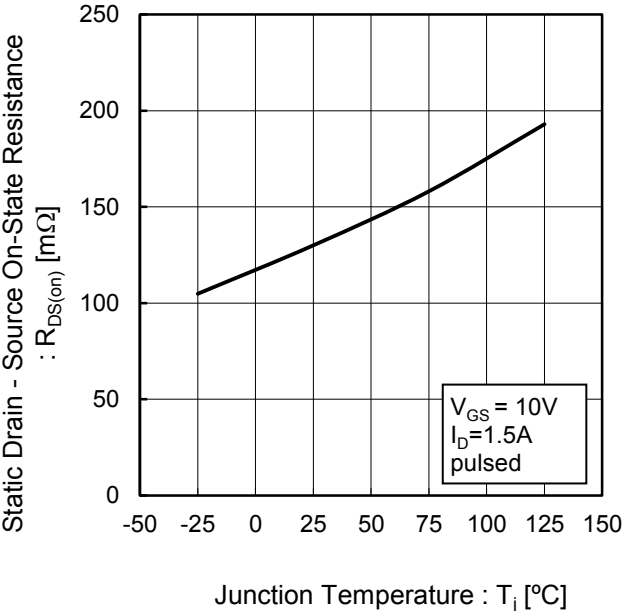


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

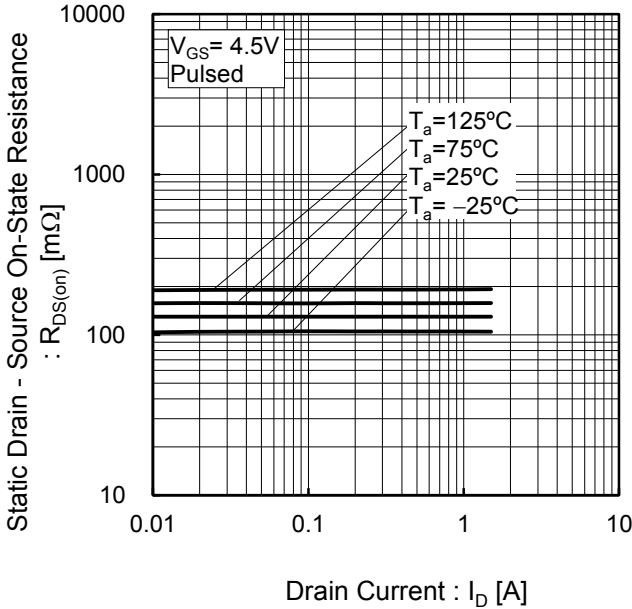


Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)

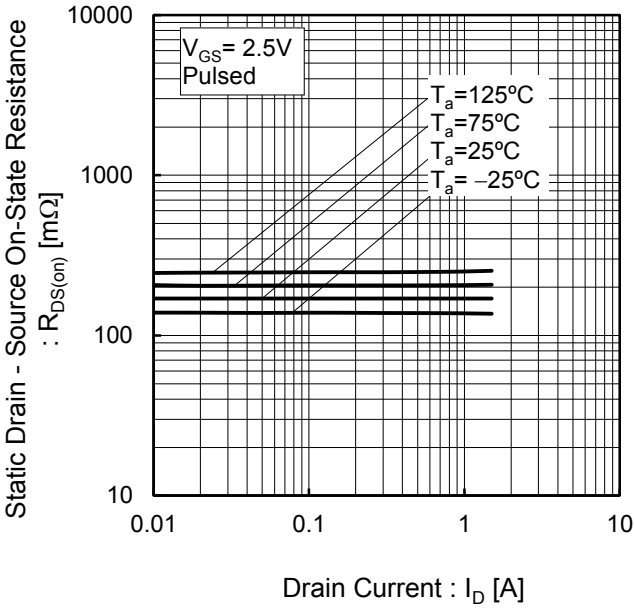


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

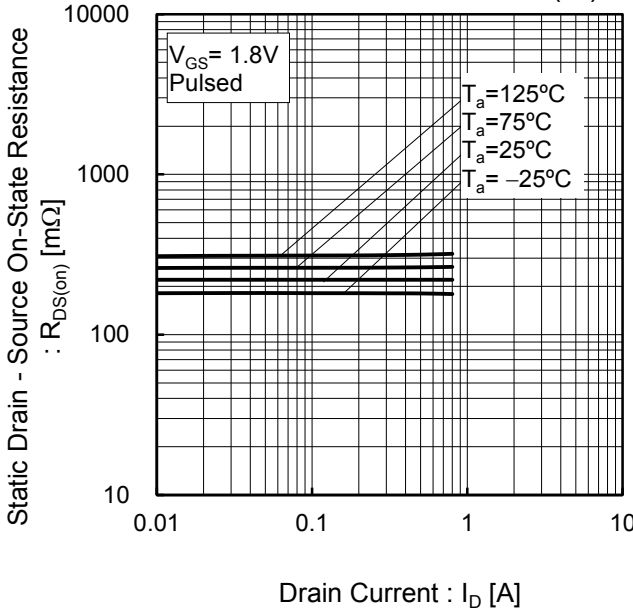
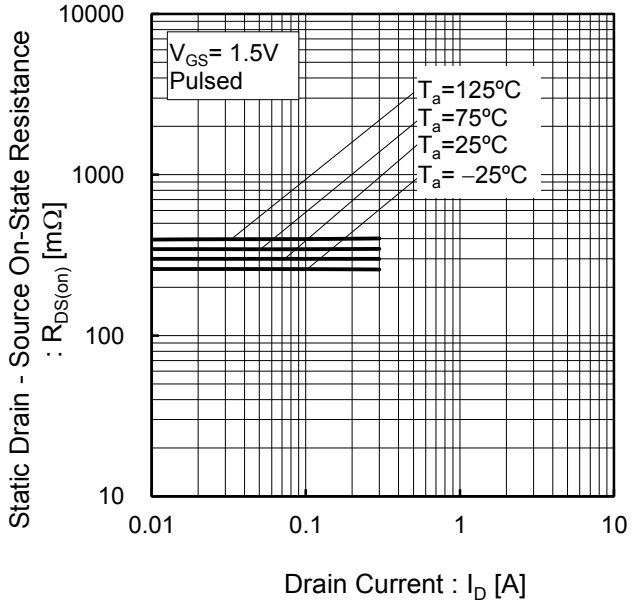


Fig.18 Static Drain - Source On - State Resistance vs. Drain Current(V)



●Electrical characteristic curves

Fig.19 Typical Capacitance
vs. Drain - Source Voltage

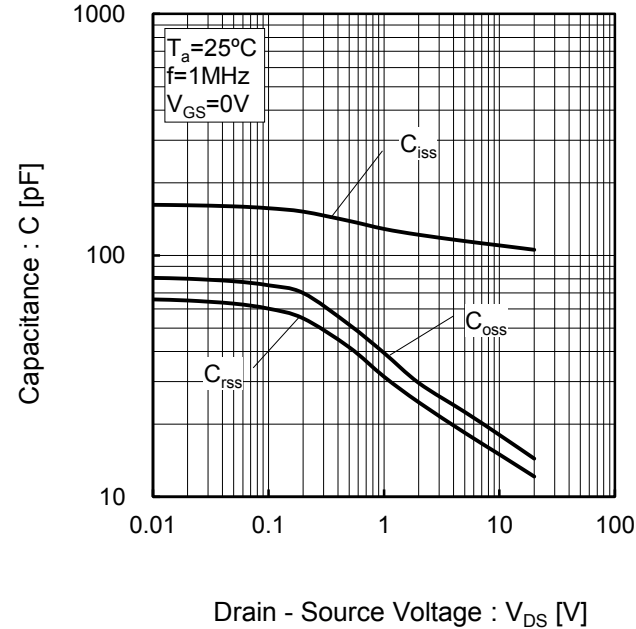


Fig.20 Switching Characteristics

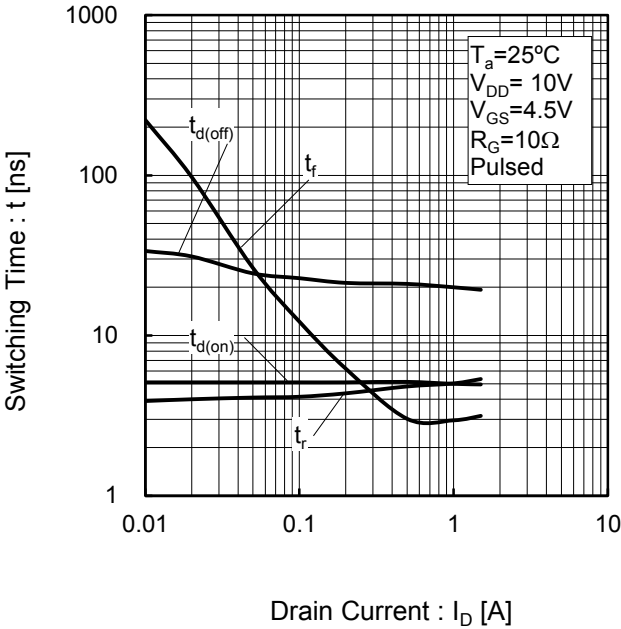


Fig.21 Dynamic Input Characteristics

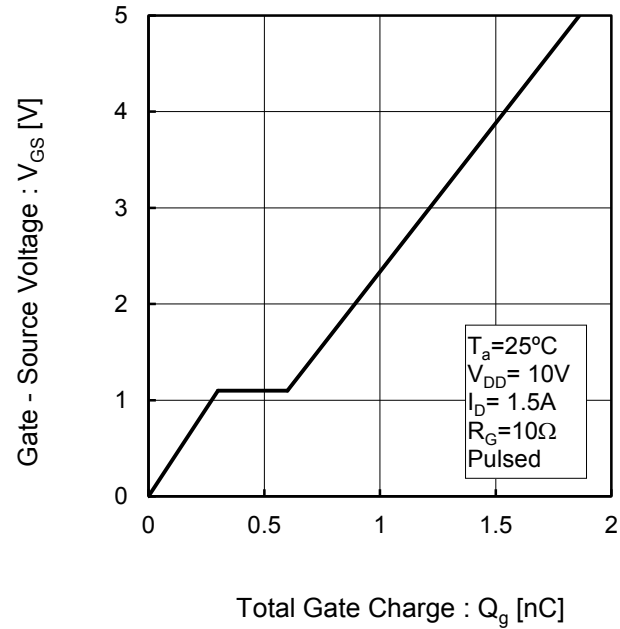
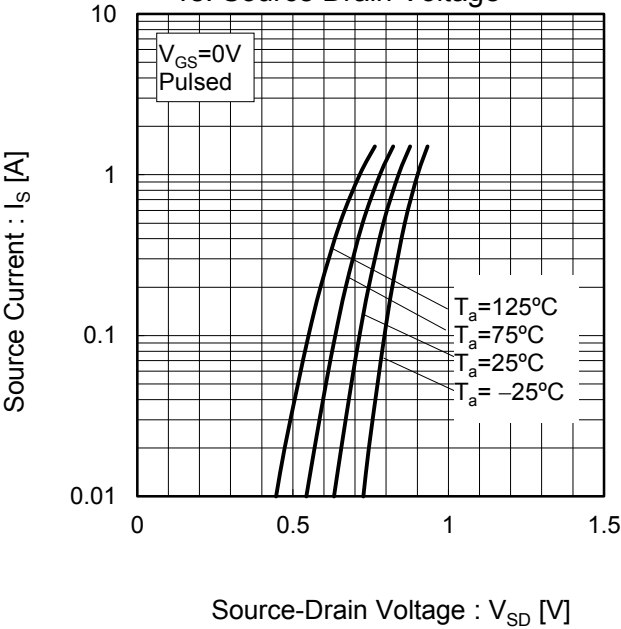


Fig.22 Source Current
vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

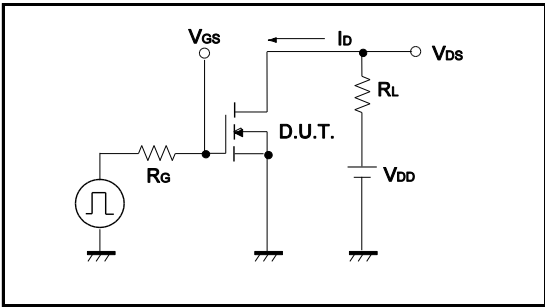


Fig.1-2 Switching Waveforms



Fig.2-1 Gate Charge Measurement Circuit

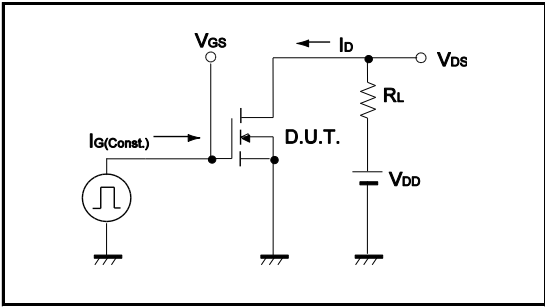
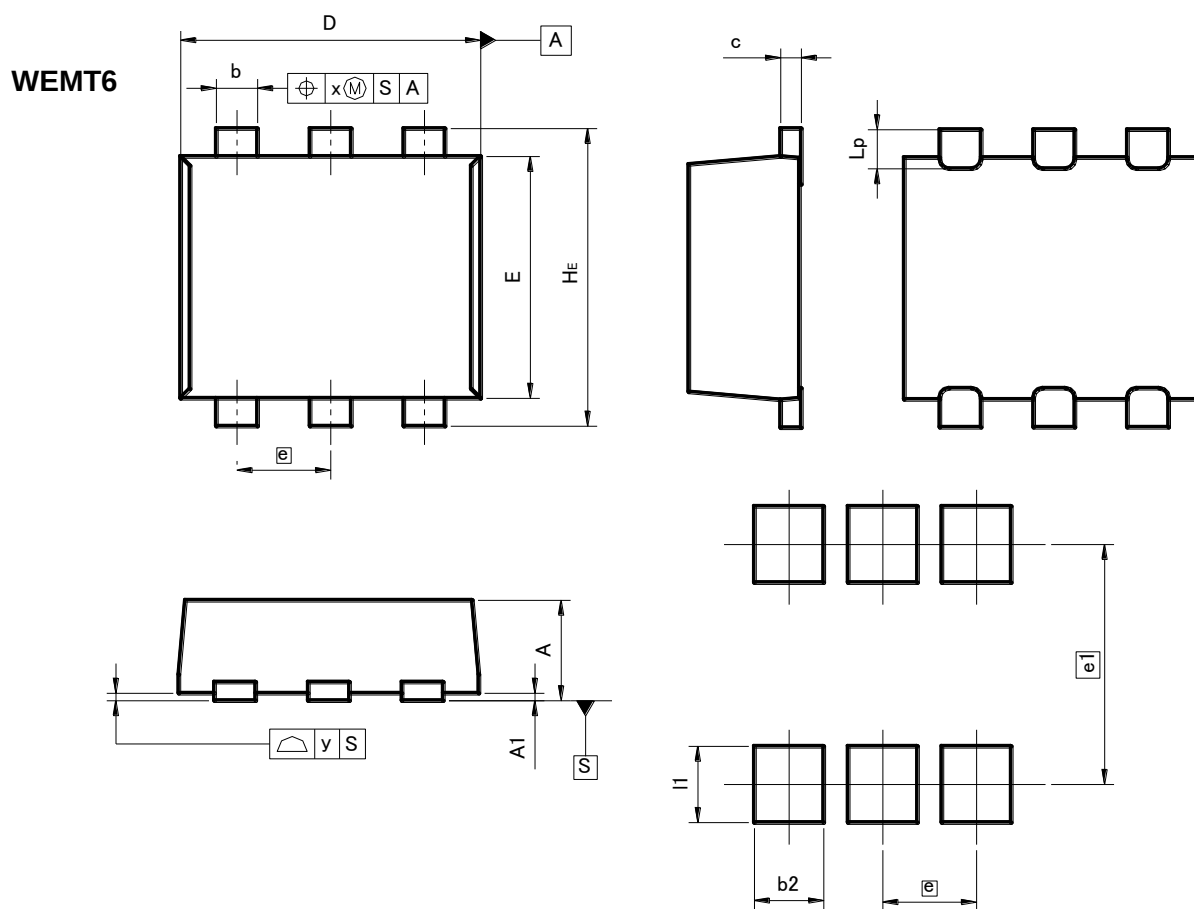


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.55	0.65	0.022	0.026
A1	0.00	0.05	0	0.002
b	0.17	0.27	0.007	0.011
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.20	1.40	0.047	0.055
e	0.50		0.02	
HE	1.50	1.70	0.059	0.067
Lp	0.11	0.31	0.004	0.012
x	—	0.10	—	0.004
y	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	1.29		0.051	
b2	—	0.37	—	0.015
l1	—	0.41	—	0.016

Dimension in mm/inches

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